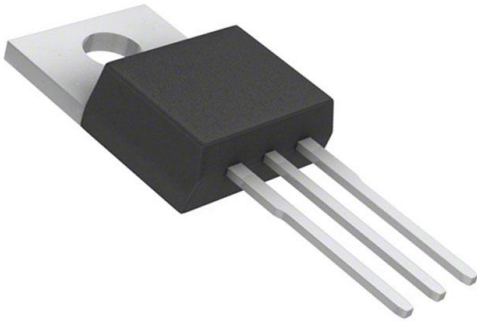


KSE3055TTU Datasheet

www.digi-electronics.com



<https://www.DiGi-Electronics.com>

DiGi Electronics Part Number	KSE3055TTU-DG
Manufacturer	onsemi
Manufacturer Product Number	KSE3055TTU
Description	TRANS NPN 60V 10A TO220-3
Detailed Description	Bipolar (BJT) Transistor NPN 60 V 10 A 2MHz 600 mW Through Hole TO-220-3



Tel: +00 852-30501935

RFQ Email: Info@DiGi-Electronics.com

DiGi is a global authorized distributor of electronic components.

Purchase and inquiry

Manufacturer Product Number:

KSE3055TTU

Series:

-

Transistor Type:

NPN

Voltage - Collector Emitter Breakdown (Max):

60 V

Current - Collector Cutoff (Max):

700µA

Power - Max:

600 mW

Operating Temperature:

150°C (TJ)

Package / Case:

TO-220-3

Base Product Number:

KSE30

Manufacturer:

onsemi

Product Status:

Obsolete

Current - Collector (Ic) (Max):

10 A

Vce Saturation (Max) @ Ib, Ic:

8V @ 3.3A, 10A

DC Current Gain (hFE) (Min) @ Ic, Vce:

20 @ 4A, 4V

Frequency - Transition:

2MHz

Mounting Type:

Through Hole

Supplier Device Package:

TO-220-3

Environmental & Export classification

Moisture Sensitivity Level (MSL):

1 (Unlimited)

ECCN:

EAR99

REACH Status:

REACH Unaffected

HTSUS:

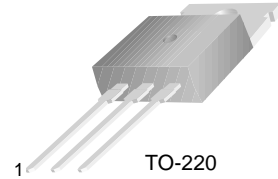
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KSE3055T

General Purpose and Switching Applications

- DC Current Gain Specified to $I_C = 10A$
- High Current Gain-Bandwidth Product : $f_T = 2MHz$ (Min.)



1.Base 2.Collector 3.Emitter

NPN Silicon Transistor

Absolute Maximum Ratings $T_C = 25^\circ C$ unless otherwise noted

Symbol	Parameter	Value	Units
V_{CBO}	Collector -Base Voltage	70	V
V_{CEO}	Collector-Emitter Voltage	60	V
V_{EBO}	Emitter-Base Voltage	5	V
I_C	Collector Current	10	A
I_B	Base Current	6	A
P_C	Collector Dissipation ($T_C = 25^\circ C$)	75	W
	Collector Dissipation ($T_a = 25^\circ C$)	0.6	W
T_J	Junction Temperature	150	$^\circ C$
T_{STG}	Storage Temperature	- 55 ~ 150	$^\circ C$

Electrical Characteristics $T_C = 25^\circ C$ unless otherwise noted

Symbol	Parameter	Test Condition	Min.	Max.	Units
BV_{CEO}	Collector-Emitter Breakdown Voltage	$I_C = 200mA, I_B = 0$	60		V
I_{CEO}	Collector Cut-off Current	$V_{CE} = 30V, I_B = 0$		700	μA
I_{CEX1} I_{CEX2}	Collector Cut-off Current	$V_{CE} = 70V, V_{BE}(off) = -1.5V$ $V_{CE} = 70V, V_{BE}(off) = -1.5V$ @ $T_C = 150^\circ C$		1 5	mA mA
I_{EBO}	Emitter Cut-off Current	$V_{EB} = 5V, I_C = 0$		5	mA
h_{FE}	*DC Current Gain	$V_{CE} = 4V, I_C = 4A$ $V_{CE} = 4V, I_C = 10A$	20 5	100	
$V_{CE}(sat)$	*Collector-Emitter Saturation Voltage	$I_C = 4A, I_B = 0.4A$ $I_C = 10A, I_B = 3.3A$		1.1 8	V V
$V_{BE}(on)$	*Base-Emitter On Voltage	$V_{CE} = 4V, I_C = 4A$		1.8	V
f_T	Current Gain Bandwidth Product	$V_{CE} = 10V, I_C = 500mA$	2		MHz

* Pulse test: $PW \leq 300\mu s$, duty cycle $\leq 2\%$ Pulse

Typical Characteristics

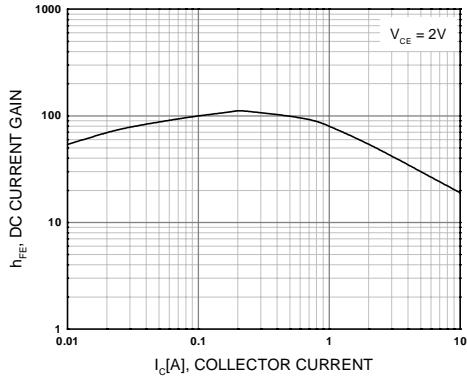


Figure 1. DC current Gain

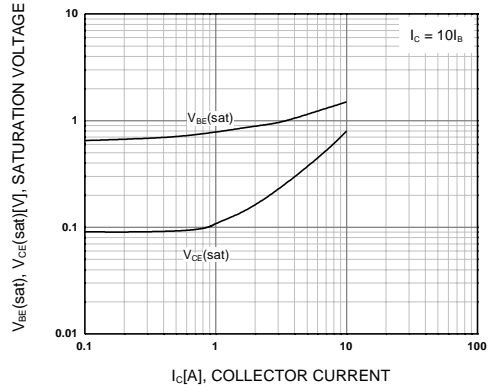


Figure 2. Base-Emitter Saturation Voltage
Collector-Emitter Saturation Voltage

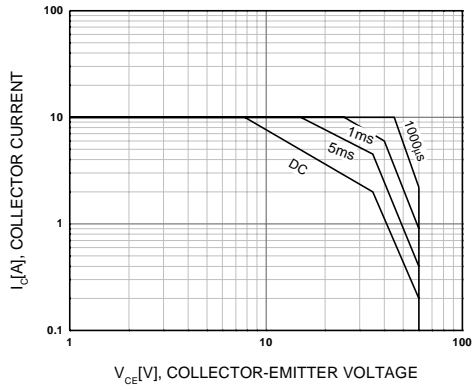


Figure 3. Safe Operating Area

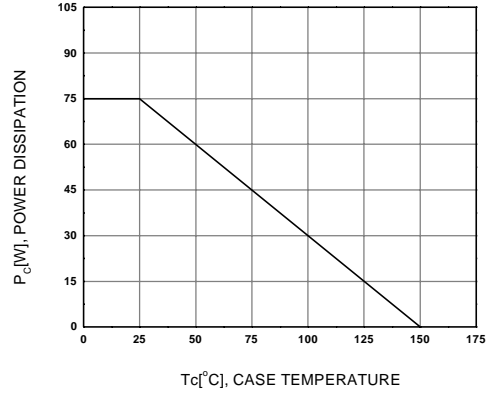
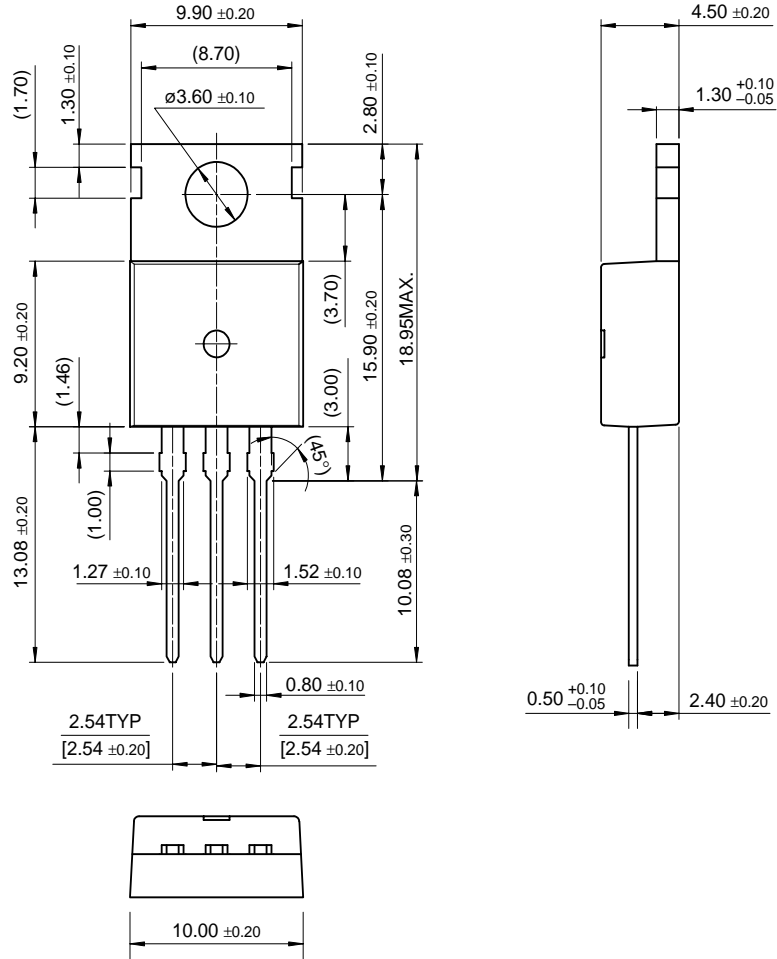


Figure 4. Power Derating

Package Dimensions

TO-220



Dimensions in Millimeters

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FASTr™	SuperSOT™-3	
GTO™	SuperSOT™-6	

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2. A critical component is any component of a life support device or system whose failure to perform can be reasonably expected to cause the failure of the life support device or system, or to affect its safety or effectiveness.

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